

**Supporting Information:**  
**Pressure-Induced Superconductivity in the Charge-Density-Wave Compound LaTe<sub>2-x</sub>Sb<sub>x</sub> (x = 0 and 0.4)**

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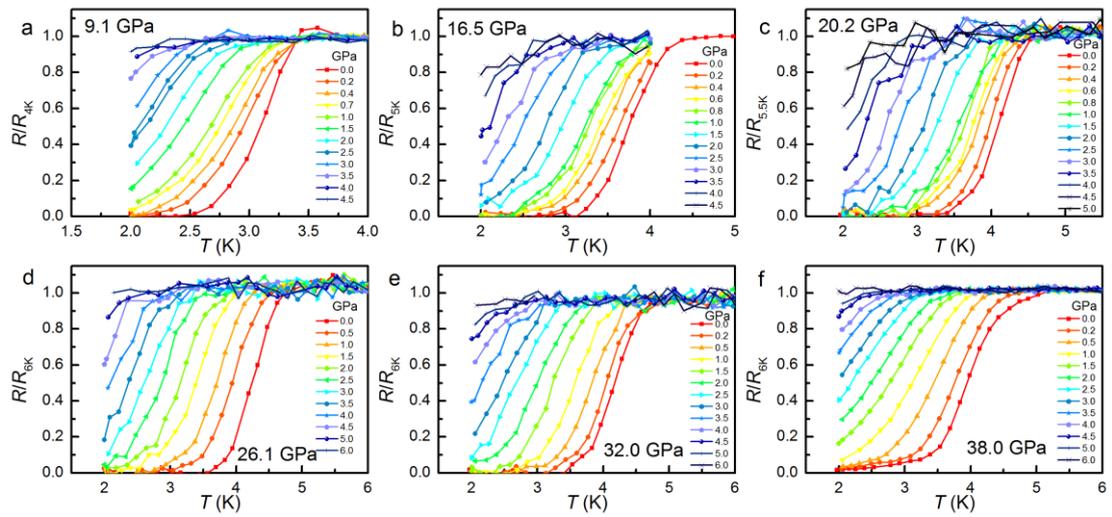
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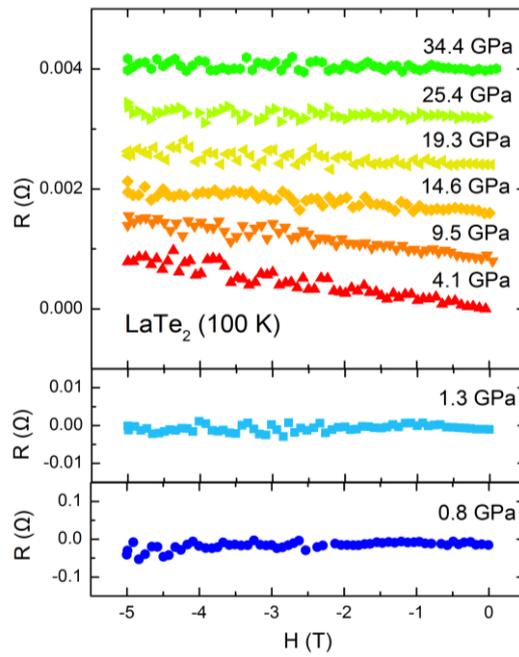
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**Table S1.** Summary of selected crystallographic parameters of LaTe<sub>2</sub> under high pressure taken from the Rietveld refinements results (space group *P4/nmm*, *Z* = 2, Te(2) (0, 0, 0)).

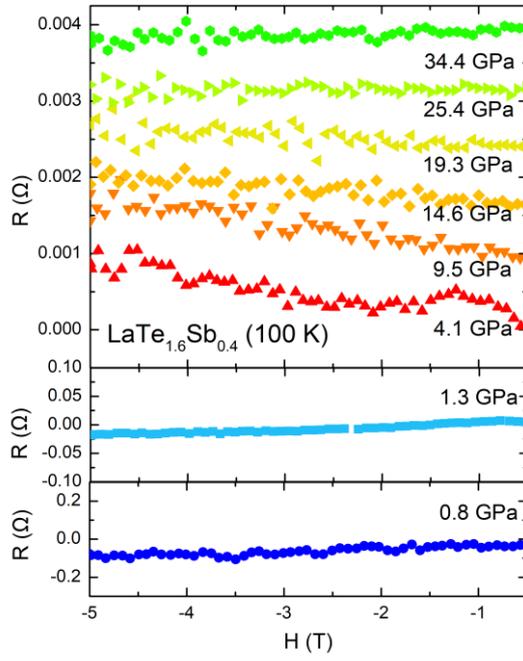
	0.2 GPa	1.5 GPa	3.1 GPa	4.6 GPa	5.9 GPa	7.3 GPa
<i>a</i> (Å)	4.558 (2)	4.532 (2)	4.501 (2)	4.476 (2)	4.466 (2)	4.450 (2)
<i>c</i> (Å)	9.214 (6)	9.160 (6)	9.091 (6)	9.057 (6)	9.014 (6)	8.993 (6)
<i>V</i> (Å <sup>3</sup> )	191.4 (2)	188.1 (2)	184.2 (2)	181.4 (2)	179.8 (2)	178.1 (2)
<i>R<sub>p</sub></i> (%)	1.10	1.59	1.65	1.65	1.56	1.72
<i>R<sub>wp</sub></i> (%)	1.58	2.22	2.19	2.30	2.21	2.47
<b>Atomic sites</b>						
La(1) (0, 0.5, z1)	0.265 (1)	0.276 (1)	0.278 (1)	0.277 (1)	0.276 (1)	0.280 (1)
Te(1) (0, 0.5, z2)	0.647 (1)	0.651 (1)	0.649 (1)	0.649 (1)	0.653 (1)	0.652 (1)
	9.3 GPa	12.0 GPa	15.9 GPa	21.6 GPa	28.5 GPa	34.8 GPa
<i>a</i> (Å)	4.432 (2)	4.418 (2)	4.385 (2)	4.344 (2)	4.286 (3)	4.246 (3)
<i>c</i> (Å)	8.952 (6)	8.895 (6)	8.809 (6)	8.713 (6)	8.583 (7)	8.500 (7)
<i>V</i> (Å <sup>3</sup> )	175.8 (2)	173.6 (2)	169.4 (2)	164.4 (2)	157.6 (3)	153.2 (3)
<i>R<sub>p</sub></i> (%)	1.39	1.30	1.58	1.80	1.84	2.76
<i>R<sub>wp</sub></i> (%)	2.04	1.95	2.48	2.82	3.03	4.52
<b>Atomic sites</b>						
La(1) (0, 0.5, z1)	0.281 (1)	0.278 (1)	0.269 (1)	0.267 (1)	0.268 (1)	0.270 (1)
Te(1) (0, 0.5, z2)	0.649 (1)	0.647 (1)	0.646 (1)	0.647 (1)	0.648 (1)	0.657 (1)



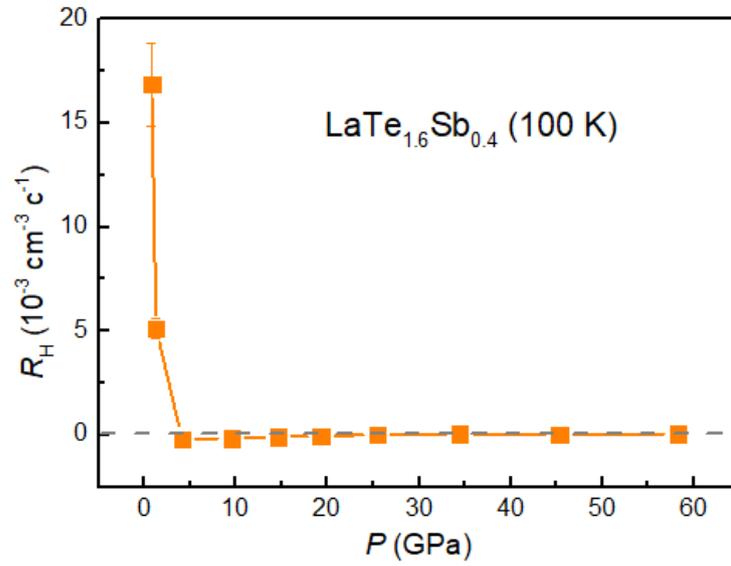
**Figure S1.** The  $R/R_{4K/5K/6K}$  around  $T_c$  under external magnetic fields of  $\text{LaTe}_2$  at different pressures.



**Figure S2.** Hall resistivity ( $R-H$ ) at 100 K of  $\text{LaTe}_2$ .



**Figure S3.** Hall resistivity ( $R$ - $H$ ) at 100 K of  $\text{LaTe}_{1.6}\text{Sb}_{0.4}$ .



**Figure S4.** Hall coefficients of  $\text{LaTe}_{1.6}\text{Sb}_{0.4}$ .